

GSDBAV19/20/21WS

High Voltage Switching Diodes

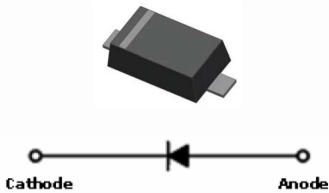
Product Description

High Voltage Switching Diode 200mW / 250V.

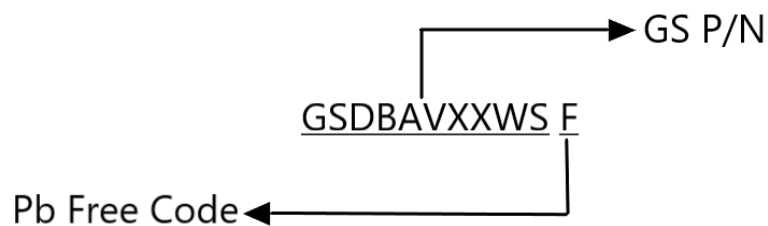
Features

- Flat Lead SOD-323 Small Outline Plastic Package
- Surface Device Type Mounting
- Moisture Sensitivity Level 1
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Band Indicates Cathode

Marking Information

Part Number	Package	Part Marking	Equivalent Circuit Diagram
GSDBAV19WSF	SOD-323	S5	
GSDBAV20WSF	SOD-323	S6	
GSDBAV21WSF	SOD-323	S7	

Ordering Information



Part Number	Package	Quantity
GSDBAV19WSF	SOD-323	3,000 PCS
GSDBAV20WSF	SOD-323	3,000 PCS
GSDBAV21WSF	SOD-323	3,000 PCS

Absolute Maximum Ratings (T_A=25°C Unless Otherwise specified)

Symbol	Parameter	Value	Units
V _{RRM}	Maximum Repetitive Reverse Voltage	250	V
I _{F(AV)}	Average Rectified Forward Current	200	mA
I _{FSM}	Non-repetitive Peak Forward Current Pulse Width=1.0 Second Pulse Width=1.0 μsecond	1.0 4.0	A
P _D	Power Dissipation	200	mW
T _J	Operating Junction Temperature	+150	°C
T _{STG}	Storage Temperature Range	-65 to + 150	°C

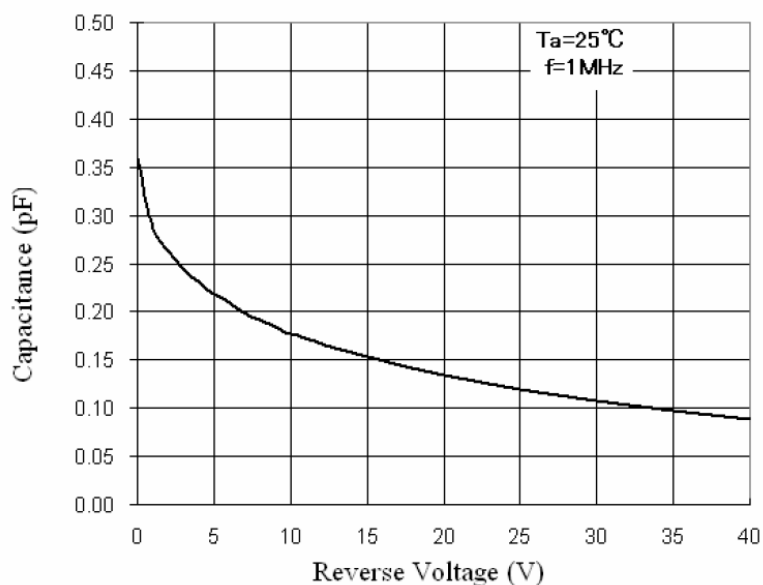
These ratings are limiting Values above which the serviceability of the diode may be impaired.

Electrical Characteristics (T_A=25°C Unless Otherwise specified)

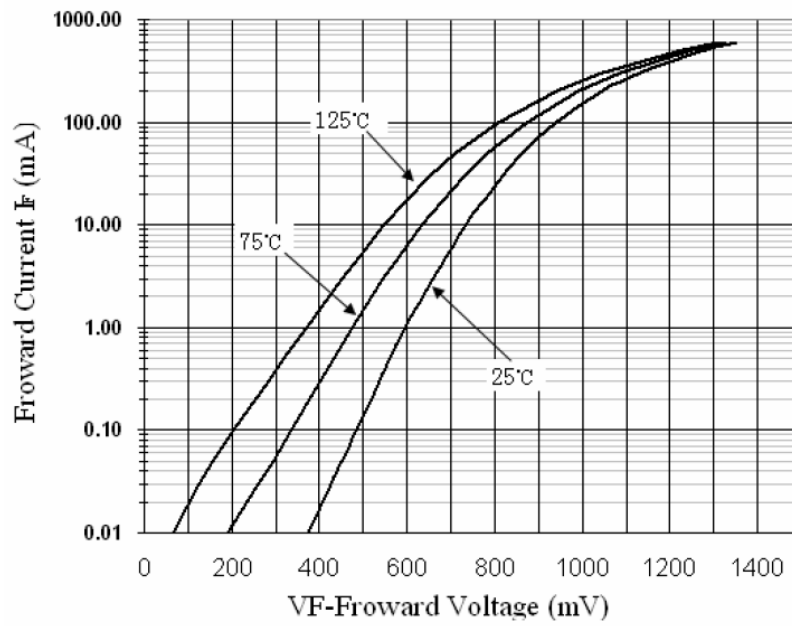
Symbol	Parameter	Test Condition	Min	Max	Units
V _F	Forward Voltage	I _F =100mA I _F =200mA	- -	1.0 1.25	V
I _R	Reverse Leakage Current GSDBAV19WS GSDBAV20WS GSDBAV21WS	V _R =100V V _R =150V V _R =200V	- - -	100 100 100	nA
B _V	Breakdown Voltage GSDBAV19WS GSDBAV20WS GSDBAV21WS	I _R =100μA	120 200 250	- - -	V
C	Capacitance	V _R =0V, f=1MHz	-	5.0	pF
T _{RR}	Reverse Recovery Time	I _F =I _R =30mA R _L =100Ω, I _{RR} =3mA	-	50	nS

Typical Characteristics

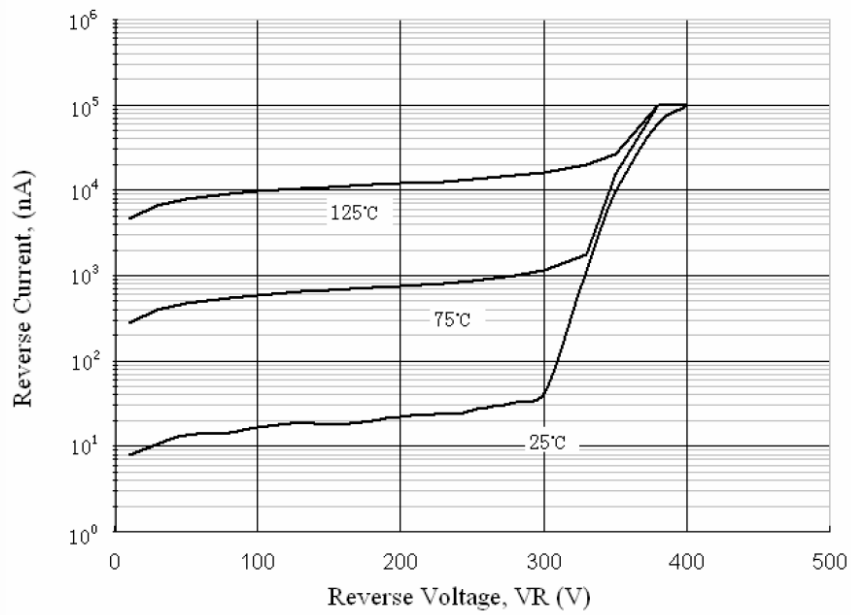
Total Capacitance



Forward Voltage vs Ambient Temperature

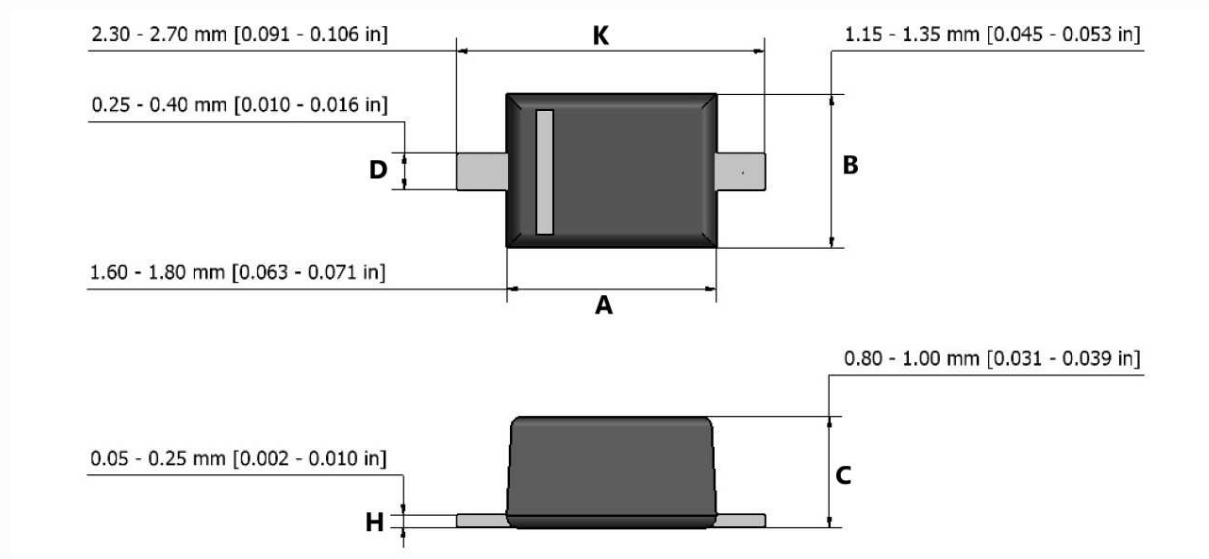


Reverse Current vs Reverse Voltage



Package Dimension

SOD-323



NOTES:

1. The above package outline is similar to JEITA SC-90.

Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.6	1.8	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.8	1	0.031	0.039
D	0.25	0.4	0.01	0.016
H	0.05	0.25	0.002	0.01
K	2.3	2.7	0.091	0.106

Pin 1.CATHODE
Pin 2.ANODE

NOTICE

Information furnished is believed to be accurate and reliable. However Globaltech Semiconductor assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties, which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Globaltech Semiconductor. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information without express written approval of Globaltech Semiconductor.

CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihs District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587